



**THE DATASHEET OF
ZVNL110ASTZ**



N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – MARCH 94

FEATURES

- * 100 Volt V_{DS}
- * $R_{DS(on)} = 3\Omega$
- * Low threshold voltage

ABSOLUTE MAXIMUM RATINGS

PARAMETER	
Drain-Source Voltage	
Continuous Drain Current at $T_{amb}=25^{\circ}\text{C}$	
Pulsed Drain Current	
Gate Source Voltage	
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	
Operating and Storage Temperature Range	

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	BV_{DSS}
Gate-Source Threshold Voltage	$V_{GS(th)}$
Gate-Body Leakage	I_{GSS}
Zero Gate Voltage Drain Current	I_{DSS}
On-State Drain Current(1)	$I_{D(on)}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$
Forward Transconductance (1)(2)	g_{fs}
Input Capacitance (2)	C_{iss}
Common Source Output Capacitance (2)	C_{oss}
Reverse Transfer Capacitance (2)	C_{rss}
Turn-On Delay Time (2)(3)	$t_{d(on)}$
Rise Time (2)(3)	t_r
Turn-Off Delay Time (2)(3)	$t_{d(off)}$
Fall Time (2)(3)	t_f

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